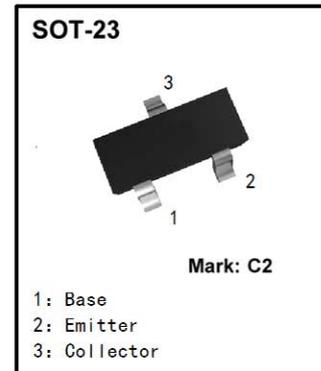


PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See BC857A for characteristics.



● Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	32	V
V_{CES}	Collector-Emitter Voltage	32	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

● Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCW30	
P_D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

• Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	32		V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 2.0 \text{ mA}, I_B = 0$	32		V
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	32		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 32 \text{ V}, I_E = 0$ $V_{CB} = 32 \text{ V}, I_E = 0, T_A = +100 \text{ }^\circ\text{C}$		100 10	nA μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$	215	500	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.30	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$	0.60	0.75	V

SMALL SIGNAL CHARACTERISTICS

NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 200 \mu A,$ $R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_W = 200 \text{ Hz}$		10	dB
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